

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

BUH1015HI

DESCRIPTION

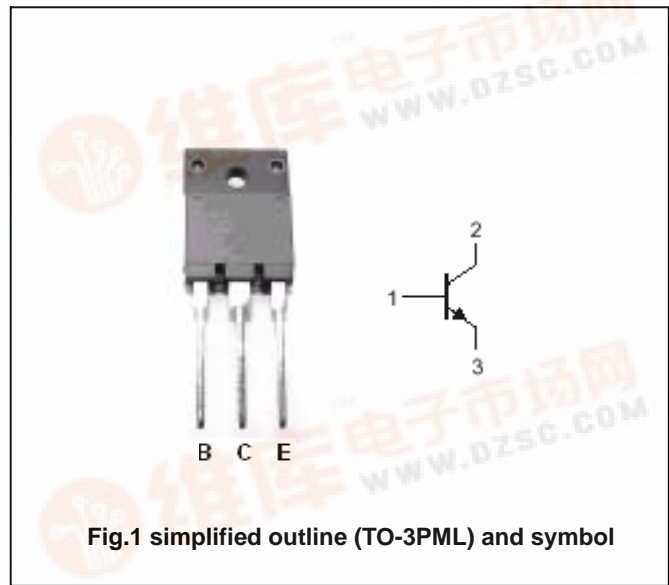
- With TO-3PML package.
- High voltage.
- High switching speed.

APPLICATIONS

- Horizontal deflection for colour TV and monitors.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	10	V
I _C	Collector current (DC)		14	A
I _{CM}	Collector current -peak	t _p <5ms	18	A
I _B	Base current		8	A
I _{BM}	Base current -peak	t _p <5ms	11	A
P _C	Collector power dissipation	T _C =25	70	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	10			V
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	700			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A; I _B =2A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A; I _B =2A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1500V; V _{BE} =0 T _j =125			0.2 2	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =10A; V _{CE} =5V T _j =100	7 5		14	
Switching times resistive load						
t _s	Storage time	I _C =10A; I _{B1} =2A; I _{B2} =-6A; V _{CC} =400V		1.5		μs
t _f	Fall time			110		ns

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-case}	Thermal resistance junction case	1.8	/W

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PACKAGE OUTLINE

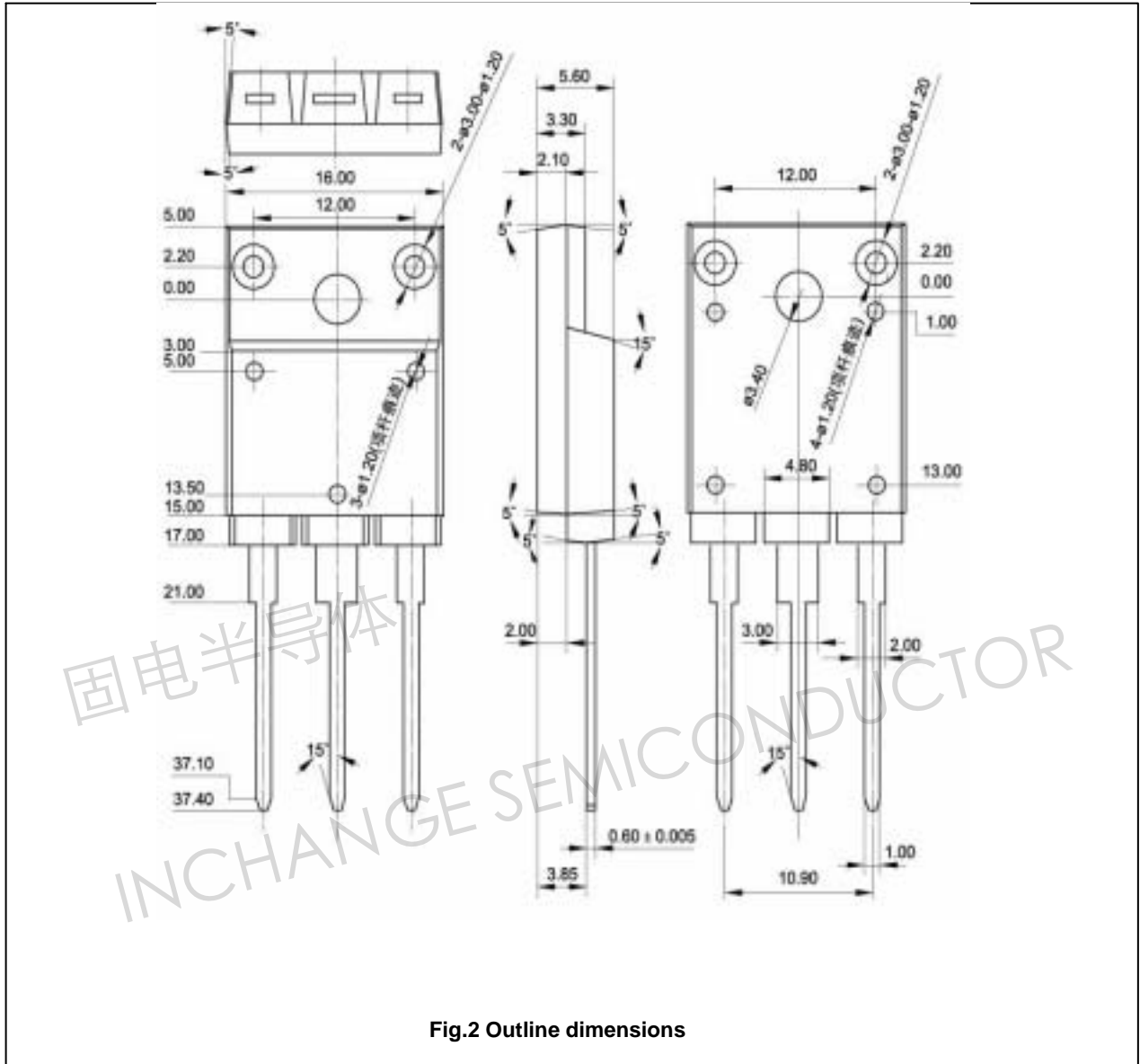


Fig.2 Outline dimensions